



PATENT ABSTRACTS OF JAPAN

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SHU SHIBUN****(54) METHOD FOR FORMING SILICIDE LAYER****(57) Abstract:**

PROBLEM TO BE SOLVED: To provide a method for forming a self-alignment silicide (salicide) layer.

SOLUTION: A method for forming a silicide layer includes a pre-amorphous implanting step before a salicide process. In the pre-amorphous implanting step, impact is applied to a silicon surface of the substrate 200 using BF₂⁺ ions, and an amorphous layer 22 is formed thereon. The salicide step includes a step for forming a metallic layer 210 on the substrate 200, a step for forming a silicide layer 212 on a silicon surface in a rapid thermal process(RTP), and a step for removing a metallic layer 210 that is not reacted.

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